3DD13003F TRANSISTOR (NPN)

TO-220F

1.BASE
2.COLLECTOR
3.EMITTER

FEATURE

- Power Switching Applications

MAXIMUM RATINGS (T_a=25 ℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	700	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current -Continuous	1.5	A
P_C	Collector Dissipation	2	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	62.5	℃/W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a= 25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= 5mA,I_E=0	700			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=10mA,I_B=0	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= 2mA, I_C=0	9			V
Collector cut-off current	I_{CBO}	V_{CB}=700V,I_E=0			1	mA
Collector cut-off current	I_{CEO}	V_{CE}=400V,I_B=0			0.5	mA
Emitter cut-off current	I_{EBO}	V_{EB}=9V, I_C=0			1	mA
DC current gain	$h_{FE(1)}$	V_{CE}=5V,I_C=0.5 A	8		40	
	$h_{FE(2)}$	V_{CE}=5V,I_C=1.5 A	5			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=1A,I_B=250mA			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=1A, I_B=250mA			1.2	V
Transition frequency	f_T	V_{CE}=10V,Ic=100mA f =1MHz	5			MHz
Fall time	t_f	I_C=1A,I_{B1}=-I_{B2}=0.2A V_{CC}=100V			0.5	μs
Storage time	t_s	Ic=250mA	2		4	μs

CLASSIFICATION OF $h_{FE(1)}$

Rank							
Range	8-10	10-15	15-20	20-25	25-30	30-35	35-40

CLASSIFICATION OF t_S

Rank	A1	A2	B1	B2
Range	2-2.5 (μs)	2.5-3(μs)	3-3.5(μs)	3.5-4 (μs)